Vishay Semiconductors

Hyperfast Rectifier, 2 A FRED Pt®



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SMA (DO-214AC)

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS			
I _{F(AV)}	2 A		
V _R	200 V		
V _F at I _F	0.75 V		
t _{rr}	25 ns		
T _J max.	175 °C		
Package	SMA (DO-214AC)		
Circuit configuration	Single		

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 $^\circ\text{C}$
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo injection, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMA (DO-214AC)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V _{RRM}		200	V
Average rectified forward current	I _{F(AV)}	T _{Sp} = 138 °C	2	^
Non-repetitive peak surge current	I _{FSM}	$T_J = 25 \ ^{\circ}C$, 6 ms square pulse	50	A .
Operating junction and storage temperatures	TJ, TStg		-55 to +175	°C

ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	200	-	-	
Forward voltage, per diode	V _F	I _F = 2 A	-	0.88	0.95	V
		I _F = 2 A, T _J = 125 °C	-	0.75	0.82	
Reverse leakage current, per diode	I _R	$V_{R} = V_{R}$ rated	-	-	2	μA
		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	1	8	
Junction capacitance	CT	V _R = 200 V	-	8	-	pF

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1

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RoHS COMPLIANT HALOGEN







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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F=1.0~A,~dI_F/dt=50~A/\mu s,~V_R=30~V$		-	24	-	
Bayaraa raaayan tima		$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	25	
Reverse recovery time		T _J = 25 °C		-	16	-	ns
		T _J = 125 °C		-	22	-	
Deck recovery current		T _J = 25 °C	$I_F = 2 \text{ A}, \\ dI_F/dt = 200 \text{ A/}\mu\text{s}, \\ V_R = 160 \text{ V}$	-	2	-	A
Peak recovery current I _R	I _{RRM}	T _J = 125 °C		-	3	-	
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	16	-	nC
	Qrr	T _J = 125 °C		-	30	-	nc

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to mount	R _{thM}	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	11	21	°C/W
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with recommended pad size	-	-	125	°C/W
Approvimete weight			0.07		g	
Approximate weight			0.002		oz.	
Marking device		Case style SMA (DO-214AC)		2	H2	

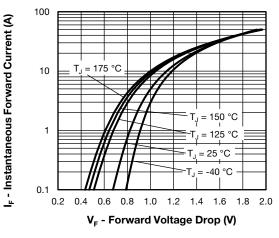


Fig. 1 - Typical Forward Voltage Drop Characteristics

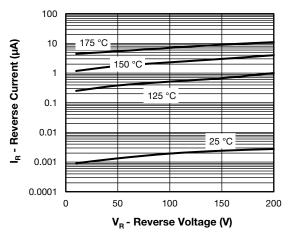
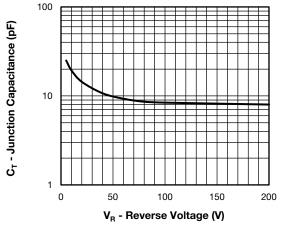


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

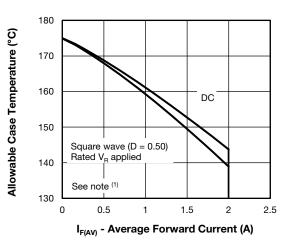


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

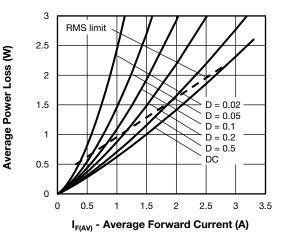
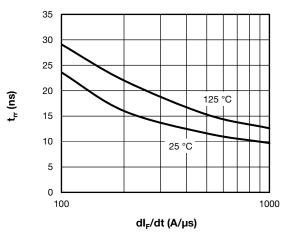


Fig. 5 - Forward Power Loss Characteristics





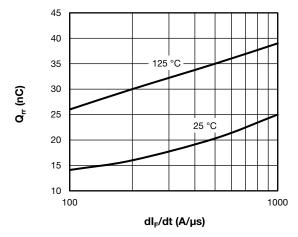


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

Revision: 23-Feb-2021

3

Document Number: 95833

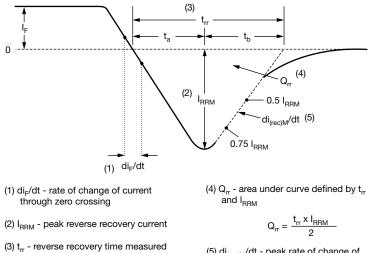
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⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $[\]begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ x \ \mathsf{V}_{\mathsf{FM}} \ at \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ x \ \mathsf{I}_{\mathsf{R}} \ (1 - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ at \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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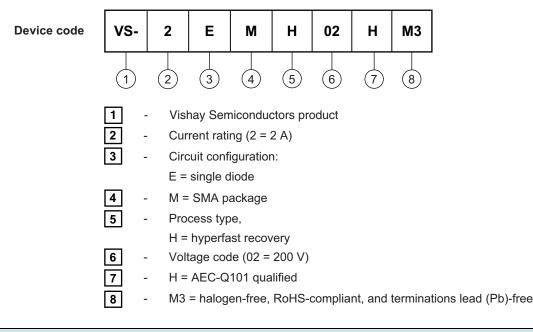


(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going $I_{\rm F}$ to point where a line passing through 0.75 $I_{\rm RRM}$ and 0.50 $I_{\rm RRM}$ extrapolated to zero current. (5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-2EMH02HM3/5AT	7500	7500	13"diameter plastic tape and reel		

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95400			
Part marking information	www.vishay.com/doc?95472			
Packaging information	www.vishay.com/doc?95404			
SPICE model	www.vishay.com/doc?96376			

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Outline Dimensions

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SMA

DIMENSIONS in inches (millimeters)

DO-214AC (SMA)





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1